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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/665,210	09/22/2003	Hidekazu Sato	031179	5736
23850	7590 09/22/2004		EXAM	INER
ARMSTRONG, KRATZ, QUINTOS, HANSON & BROOKS, LLP			HO, TU TU V	
1725 K STRE SUITE 1000	ET, NW		ART UNIT	PAPER NUMBER
	ON, DC 20006		2818	

DATE MAILED: 09/22/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

		AVX
	Application No.	Applicant(s)
Office Action Comment	10/665,210	SATO ET AL.
Office Action Summary	Examiner	Art Unit
The MAN INC DATE - EAL!	Tu-Tu Ho	2818
The MAILING DATE of this communication app Period for Reply	lears on the cover sheet with t	the correspondence address
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period v - Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply y within the statutory minimum of thirty (36 will apply and will expire SIX (6) MONTHS , cause the application to become ABANI	be timely filed 0) days will be considered timely. 5 from the mailing date of this communication. DONED (35 U.S.C. § 133).
Status		
 1) Responsive to communication(s) filed on <u>02 Sectors</u> 2a) This action is FINAL. 2b) This 3) Since this application is in condition for alloward closed in accordance with the practice under Extended 	action is non-final. nce except for formal matters	
Disposition of Claims		
 4) ☐ Claim(s) 1-25 is/are pending in the application. 4a) Of the above claim(s) 2,3,5,8,10 and 12-25 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1,4,6,7,9 and 11 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/or 	is/are withdrawn from consid	deration.
Application Papers		
9) The specification is objected to by the Examine 10) The drawing(s) filed on 22 September 2003 is/3 Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Examine 10.	are: a) accepted or b) of drawing(s) be held in abeyance. tion is required if the drawing(s)	See 37 CFR 1.85(a). is objected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
a) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Apprity documents have been received in the contract of the cont	lication No ceived in this National Stage
Attachment(s) 1) ☑ Notice of References Cited (PTO-892) 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) ☑ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 09/22/2003.	Paper No(s)/M	nmary (PTO-413) Iail Date mal Patent Application (PTO-152)

DETAILED ACTION

Oath/Declaration

1. The oath/declaration filed on 09/22/2003 is acceptable.

Specification

2. The title of the invention is not descriptive (there are more than 300 thousands patented inventions and patent application publications with "semiconductor device" in the title and 750 thousands with "semiconductor" in the title). A new title is required that is clearly indicative of the invention to which the claims are directed. The examiner suggests that the title be changed to "Bipolar Transistor" or "Semiconductor Device Having Collector".

Election/Restriction

Applicant's election without traverse of Species I of Group I, claims 1, 4, 6, 7, 9, and 11, in Paper filed 09/02/2004 is acknowledged. Accordingly, claims 2-3, 5, 8, 10, and 12-25 are withdrawn from consideration.

Claim Rejections

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(e) the invention was described in

(1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or

Application/Control Number: 10/665,210

Art Unit: 2818

(2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

The following is a quotation of 35 U.S.C. §103(a) which forms the basis for all obviousness rejections set forth in this Office action:

- (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. Claims 1, 4, 6, 7, 9, and 11 are rejected under under 35 U.S.C. 102(e) as anticipated by or, in the alternative, under 35 U.S.C. 103(a) as obvious over Oda et al. U.S. Patent 6,482,710.

Oda discloses in Figure 5C and respective portions of the specification a semiconductor device substantially as claimed.

Referring to claim 1, Oda discloses a semiconductor device, comprising:

a semiconductor substrate (1) having a collector (18) formed thereon;

insulation films (7/8) formed on said semiconductor substrate, said insulation films having an opening (defined by film 14/15) formed on a portion that corresponds to the collector (18);

a conductive film (9) formed on said insulation films (7/8);

a semiconductor film (14/15) formed inside the opening, a portion (center region of portion 14) in contact with the collector (18) of said semiconductor film being formed of single crystal (column 10, lines 5-14), a portion (15) in contact with said conductive film (9) of said semiconductor film being formed of polycrystal (column 10, lines 5-14); and

Application/Control Number: 10/665,210

Art Unit: 2818

an emitter (20/19) formed on said semiconductor film.

However, Oda fails to explicitly disclose that the portion (15) in contact with said conductive film (9) being one to two times as thick as the portion (14) in contact with the collector (18). Nevertheless, as can be seen from Fig. 5C, the portion (15) in contact with said conductive film (9) appears to be one to two times as thick as the portion (the central region of portion 14) in contact with the collector (18). Note also that portions 14 and 15 are formed in the same process (column 10, lines 5-14) and that an upper surface of the central region of portion 14 contacts layer 20 whose upper surface is planar with an upper surface of the outer regions of portion 14 which is thinner than portion 15, thereby causing the appearance that the portion (15) in contact with said conductive film (9) being one to two times as thick as the portion (14) in contact with the collector (18).

Referring to claim 4, Oda further discloses that said semiconductor film (14/15) is a film comprising at least a film selected from a group including an SiGe composed crystal film (crystal silicon germanium, column 10, lines 5-14) and an SiGeC composed crystal film.

Referring to **claim 6**, Oda further discloses that said conductive film (9) is a film selected from a group including a polycrystalline silicon film (column 8, lines 25-30) and an aluminum film.

Referring to **claim 7**, although Oda does not discloses that said insulation film (7/8) is a silicon oxide film, Oda discloses that insulation film 7/8 comprises a silicon oxide film (column 8, lines 24-26). Since either a silicon-oxide insulation film as claimed or an insulation film comprising a silicon oxide film as disclosed by Oda functions as an insulation film, the change from one to the other would have been obvious at the time the invention was made.

Art Unit: 2818

Referring to claim 9, Oda further discloses a second insulation film (10 or 17) that insulates between said conductive film (9) and the emitter (20/19).

Referring to claim 11, Oda further discloses that said second insulation film (10 or 17) is a film selected from a group including a silicon oxide film (column 8, lines 29-30) and a silicon nitride film.

Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tu-Tu Ho whose telephone number is (571) 272-1778. The examiner can normally be reached on 6:30 am - 5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, DAVID NELMS can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Tu-Tu Ho September 15, 2004